ABSTRACT OF THE DISCLOSURE

It is disclosed a cleaning liquid for stripping and dissolving a photoresist pattern having a film thickness of 10 - 150 μm, which contains (a) 0.5 - 15 mass % of a quaternary ammonium hydroxide, such as tetrapropylammonium hydroxide and tetrabutylammonium hydroxide, (b) 65 - 97 mass % of a water-soluble organic solvent, such as dimethylsulfoxide or a mixed solvent thereof with N-methyl-2-pyrrolidone, sulforane, etc., and (c) 0.5 - 30 mass % of water, and a method for treating a substrate therewith.